

What is claimed is:

1. A method for clearing slurry from a polishing pad in a CMP process, comprising:
placing a wafer substrate in contact with a polishing pad;
rotating said polishing pad;
providing a slurry dispense bar including a high pressure spray portion and a
slurry dispense portion located over the polishing pad;
dispensing slurry from said slurry dispense bar on said polishing pad while said
pad is rotating with said wafer substrate in contact with said pad;
terminating slurry dispense; and
spraying a high pressure fluid to remove slurry from between said wafer
substrates and said pad with said high pressure spray portion of said slurry dispense bar.
2. The method of claim 1, wherein said high pressure spray includes water and is
between 10 and 20 PSI.
3. The method of claim 2, wherein said high pressure spray is about 14 PSI.
4. The method of claim 1, including:
rotating said pad at a high speed during said spraying step.
5. The method of claim 4, wherein said high speed is between 90 and 120 RPMs.

6. The method of claim 1, wherein said slurry dispense bar includes a splash guard located above said high pressure spray portion.

7. The method of claim 6, wherein said slurry dispense portion is located above said splash guard.

8. The method of claim 7, including a second slurry dispense portion located above said splash guard.

9. *Sub A 37* A method for clearing slurry from a polishing pad in a CMP process, comprising:
placing a wafer substrate in contact with a polishing pad;
rotating said polishing pad at a first speed;
dispensing slurry onto said polishing pad while said pad is rotating with said wafer substrates in contact with said pad;
terminating slurry dispense;
spraying a high pressure fluid around said wafer substrate to remove slurry from between said wafer substrate and said pad using said high pressure spray portion of said slurry dispense bar; and
rotating said pad at a second speed during said spraying step.

10. The method of claim 9, wherein said high pressure spray is between 10 and 20 PSI.

11. The method of claim 10, wherein said second speed is between 60 and 200 RPMs.

12. The method of claim 10, wherein said second speed is between 90 and 120 RPMs.

13. A system for controlling the removal of a substrate in a CMP polishing system, comprising:

a polishing pad located on a platen, said platen operable at a first speed and a second speed, said second speed being higher than said first speed;

a wafer carrier for biasing a wafer substrate against said polishing pad;

a slurry dispense bar including a high pressure spray portion and a slurry dispense portion, said slurry dispense bar located above said polishing pad during the wafer polishing operation;

a control device for controlling the dispense of slurry from said slurry dispense bar at a first time and for controlling the dispense of high pressure fluid from said slurry dispense bar at a second time, wherein said control device additionally controls the rotation of said platen to rotate at said first speed during said first time and said second speed during said second time.

14. The system of claim 13, wherein said first speed is from 30 RPMs up to 60 RPMs and wherein said second speed is greater than 60 RPMs.

15. The system of claim 14, wherein said second speed is between 90 and 120 RPMs.

16. The system of claim 15, wherein said high pressure fluid is sprayed from 10 to 20 PSI.

17. The system of claim 16, wherein said high pressure fluid is deionized water.

18. The system of claim 13, wherein said slurry dispense bar includes a second slurry dispense portion.

19. The system of claim 18, wherein said second slurry dispense portion can be used to dispense deionized water.

20. The system of claim 18 including a second wafer carrier, wherein said slurry dispense bar is located over said pad between the first wafer carrier and said second wafer carrier.